

Side Face Silicon Phototransistor PT5529B/L2/H2-F354



Features

- Fast response time
- High photo sensitivity
- Pb free
- This product itself will remain within RoHS compliant version.
- Compliance with EU REACH
- Compliance Halogen Free .(Br <900 ppm ,Cl <900 ppm , Br+Cl < 1500 ppm)

Description

- PT5529B/L2/H2-F354 is a high speed and high sensitive dual phototransistor molded in a black plastic package with plat side view.
- The device is spectrally matched with IR emitters.

Applications

- Mouse
- Optoelectronic Switch
- Photo Interrupter

Device Selection Guide

LED Part No	Chip Materials	Lens Color
PT5529B/L2/H2-F354	Silicon	Black

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Collector-Voltage	V _{ECO}	5	V
Collector Current	I _c	20	mA
Operating Temperature	T _{opr}	-40 ~ +85°C	°C
Storage Temperature	T _{stg}	-40 ~ +85°C	°C
Lead Soldering Temperature(*1)	T _{sol}	260	°C
Power Dissipation at (or below) 25°C Free Air Temperature	P _D	75	mW

Notes: *1:Soldering time ≤ 5 seconds.

Electro-Optical Characteristics (Ta=25°C)

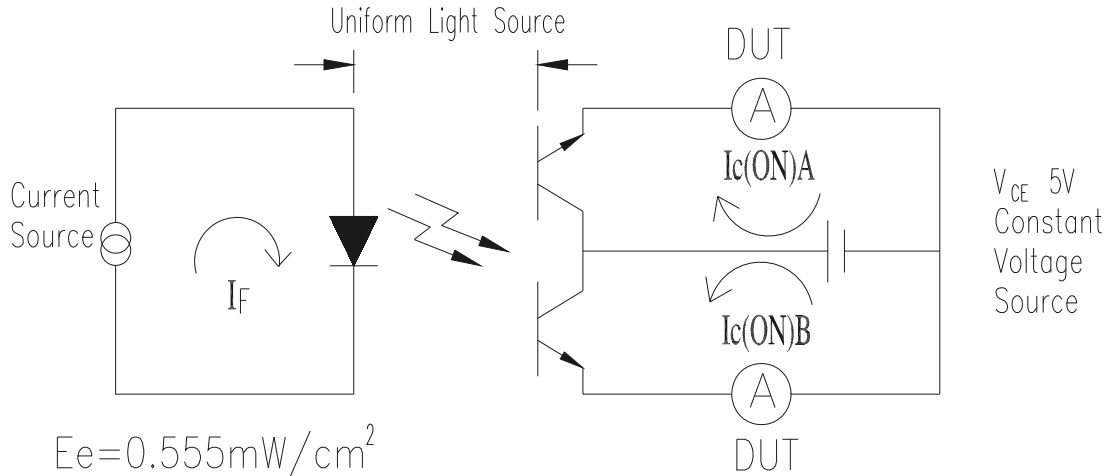
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Collector – Emitter Breakdown Voltage	BV_{CEO}	$I_C=100\mu A$ $E_e=0mW/cm^2$	30	---	---	V
Emitter-Collector Breakdown Voltage	BV_{ECO}	$I_E=100\mu A$ $E_e=0mW/cm^2$	5	---	---	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2mA$ $E_e=1mW/cm^2$	---	---	0.4	V
Rise Time	t_r	$V_{CE}=5V$ $I_C=1mA$ $R_L=1000\Omega$	---	15	---	μS
Fall Time	t_f		---	15	---	
Collector Dark Current	I_{CEO}	$E_e=0mW/cm^2$ $V_{CE}=20V$	---	---	100	nA
On State Collector Current	$I_{C(on)}$	$V_{CE}=5V,$ $E_e=0.555mW/cm^2$	129	---	1085	μA
Wavelength of Peak Sensitivity	λ_p	---	---	940	---	nm
Rang of Spectral Bandwidth	$\lambda_{0.5}$	---	760	---	1100	nm

Test Method For On State Collector Current :

Condition : $E_e=0.555\text{mW}/\text{cm}^2$, $V_{CE}=5\text{V}$

Test Item : Collector Current [$I_{C(ON)}$]

Unit : μA



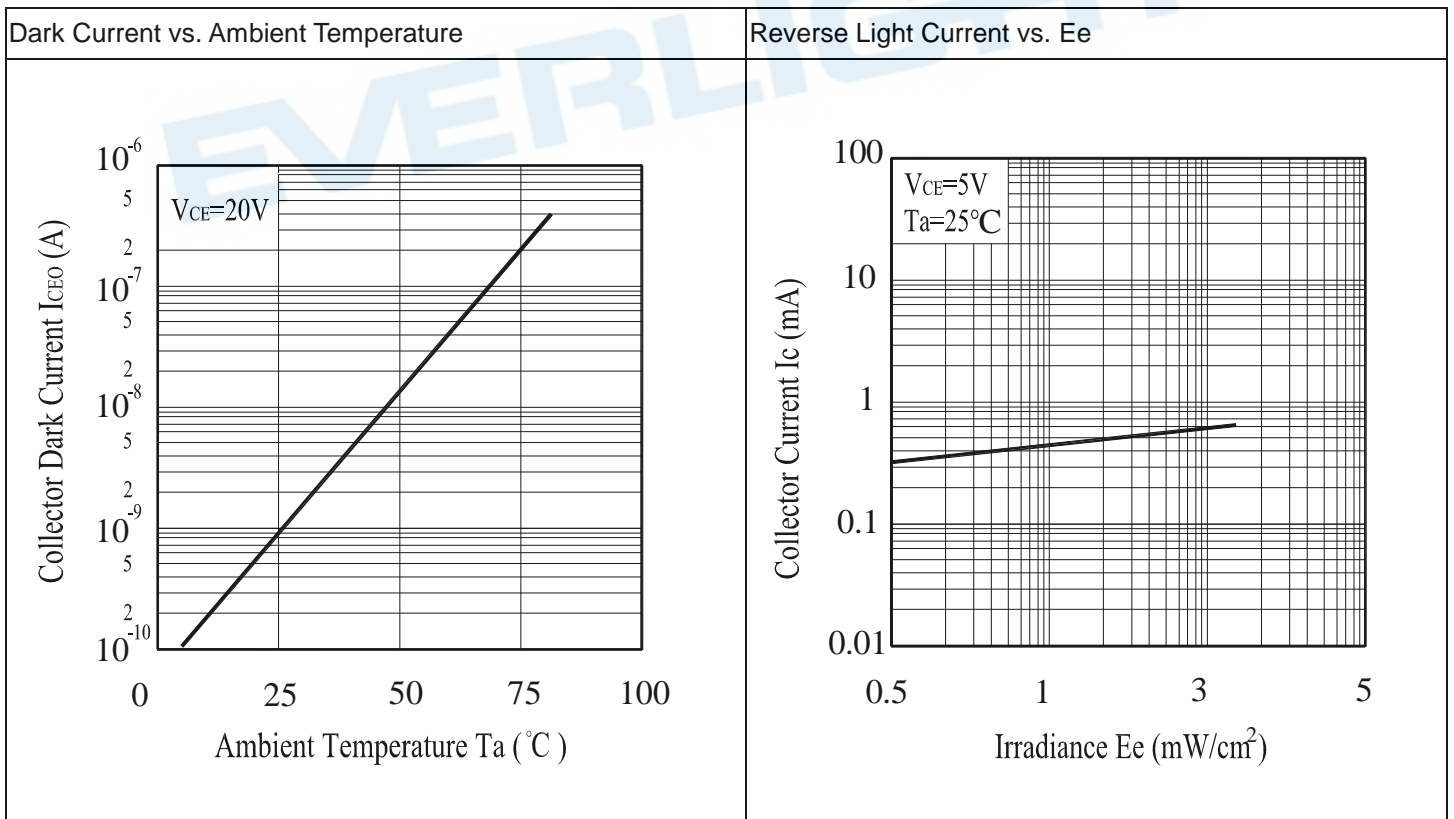
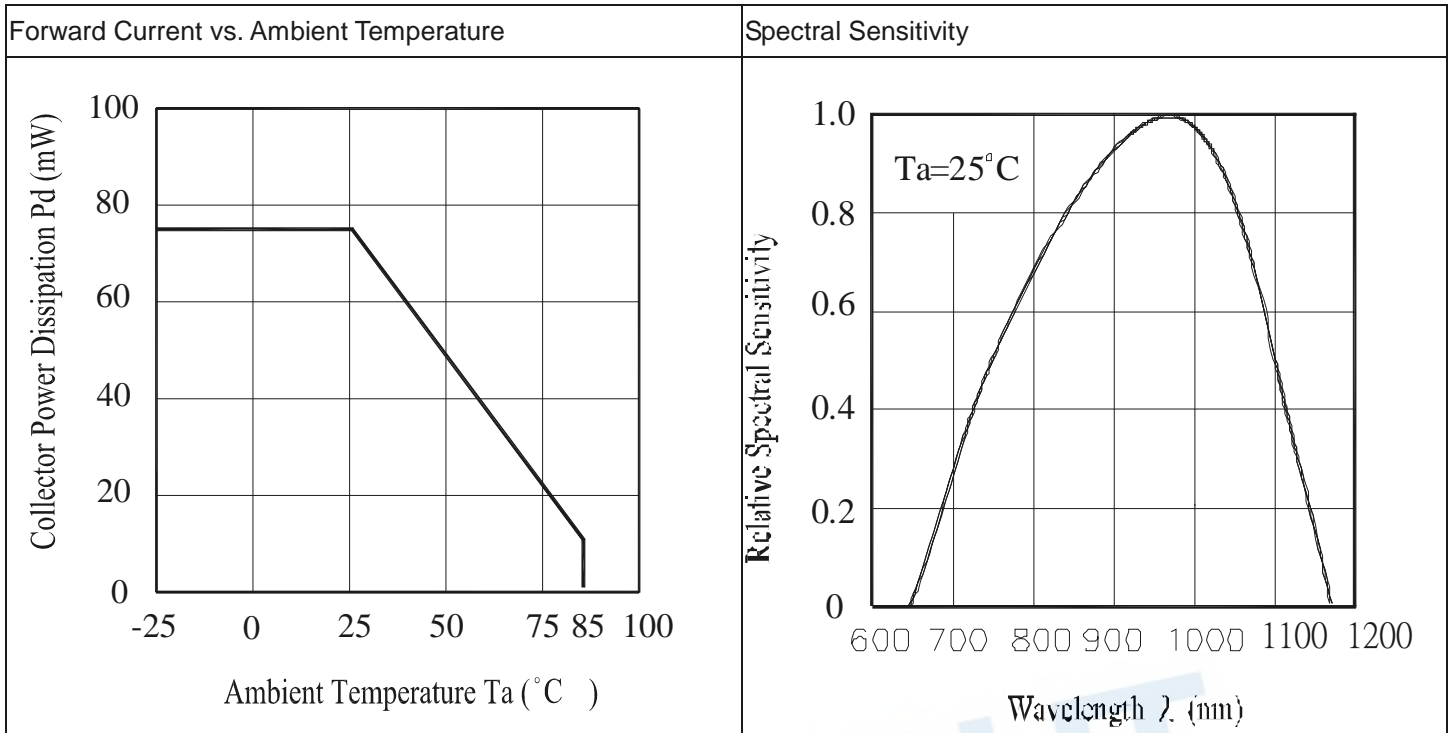
To Distinguish Intensity:

Condition: $V_{CE}=5\text{V}$ $E_e=0.555\text{mW}/\text{cm}^2$

Ranks

Ranks	Symbol	Min	Typ	Max	Unit	Text Condition
A1	$I_{C(ON)}$	129	-----	226	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A2	$I_{C(ON)}$	195	-----	306	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A3	$I_{C(ON)}$	262	-----	380	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A4	$I_{C(ON)}$	330	-----	461	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A5	$I_{C(ON)}$	398	-----	544	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A6	$I_{C(ON)}$	468	-----	625	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A7	$I_{C(ON)}$	536	-----	703	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A8	$I_{C(ON)}$	604	-----	785	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A9	$I_{C(ON)}$	673	-----	862	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A10	$I_{C(ON)}$	742	-----	944	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A11	$I_{C(ON)}$	812	-----	1018	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$
A12	$I_{C(ON)}$	882	-----	1085	μA	$E_e=0.555\text{mW}/\text{cm}^2$ $V_{CE}=5\text{V}$

Typical Electro-Optical Characteristics Curves



Typical Electro-Optical Characteristics Curves

Fig.5 Relative Collector Current vs. Ambient Temperature

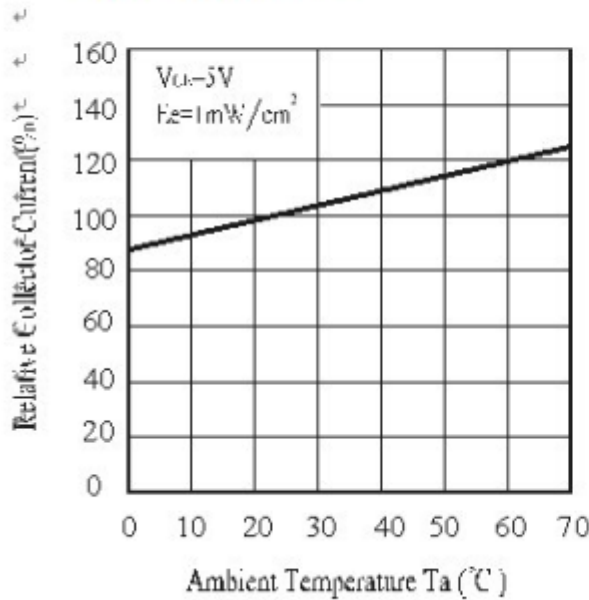
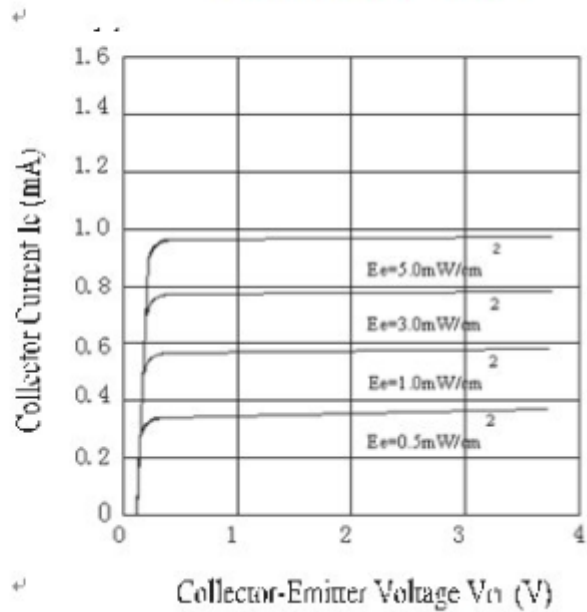


Fig.6 Collector Current vs. Collector-Emitter Voltage



Reliability Test Item And Condition

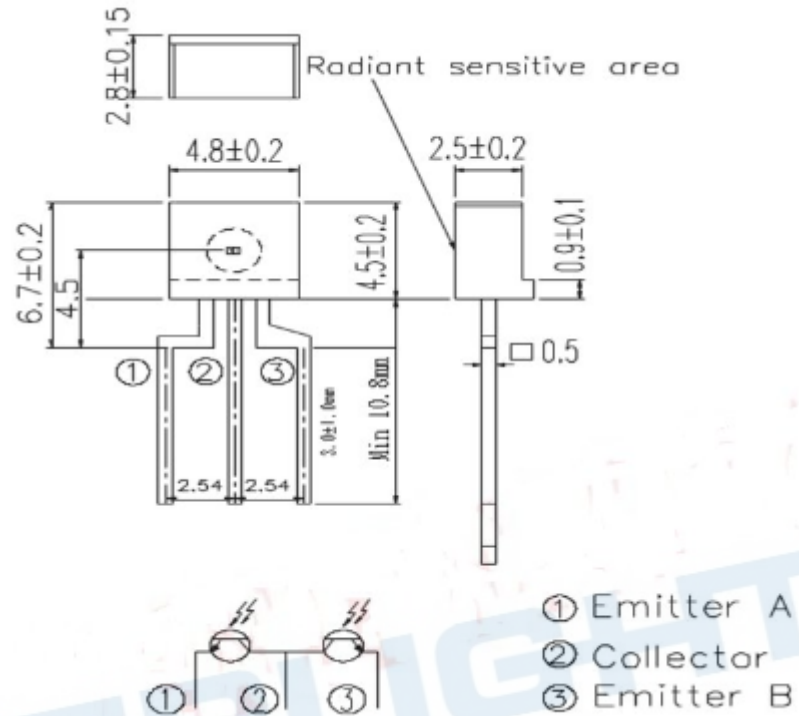
The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgement Criteria	Ac/Re
1	Solder Heat	TEMP. : 260°C	10secs	22pcs		0/1
2	Temperature Cycle	H : +100°C ↓ 15mins 5mins ↑ 5mins L : -40°C ↓ 15mins	300Cycles	22pcs		0/1
3	Thermal Shock	H : +100°C ↓ 5mins 10secs ↑ 5mins L : -10°C	300Cycles	22pcs	$I_{c(ON)} \leq L \times 0.8$	0/1
4	High Temperature Storage	TEMP. : +100°C	1000hrs	22pcs	L : the initial test value	0/1
5	Low Temperature Storage	TEMP. : -40°C	1000hrs	22pcs		0/1
6	DC Operating Life	VCE=5V	1000hrs	22pcs		0/1
7	High Temperature / High Humidity	85°C / 85% R.H	1000hrs	22pcs		0/1

Package Dimension

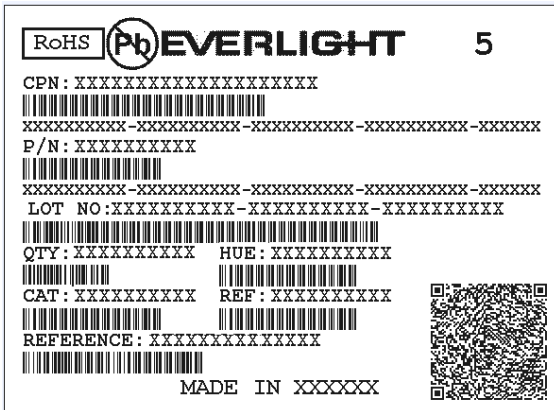


Note: Tolerances unless dimensions $\pm 0.25\text{mm}$

Packing Quantity Specification

1. 1000PCS/1Bag,10Bag/1Box
2. 10Boxes/1Carton

Label Form Specification



- CPN: Customer's Product Number
- P/N: Product Number
- QTY: Packing Quantity
- CAT: Luminous Intensity Rank
- HUE: Dom. Wavelength Rank
- REF: Forward Voltage Rank
- LOT No: Lot Number
- X: Month
- Reference: Identify Label Number

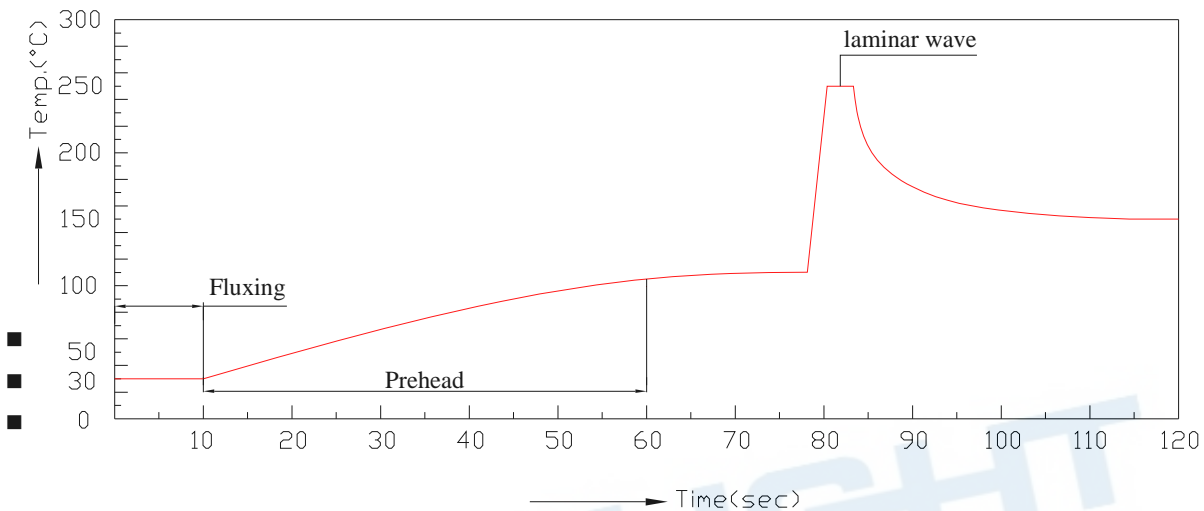
Notes

1. Lead Forming
 - During lead formation, the leads should be bent at a point at least 3mm from the base of the epoxy bulb.
 - Lead forming should be done before soldering.
 - Avoid stressing the Phototransistor package during leads forming. The stress to the base may damage the Phototransistor's characteristics or it may break the Phototransistor.
 - Cut the Phototransistor lead frames at room temperature. Cutting the lead frames at high temperatures may cause failure of the Phototransistor.
 - When mounting the Phototransistor onto a PCB, the PCB holes must be aligned exactly with the lead position of the Phototransistor. If the Phototransistor are mounted with stress at the leads, it causes deterioration of the epoxy resin and this will degrade the Phototransistor.
2. Storage
 - The Phototransistor should be stored at 30°C or less and 70%RH or less after being shipped from Everlight and the storage life limits are 3 months. If the Phototransistor are stored for 3 months or more, they can be stored for a year in a sea Phototransistor container with a nitrogen atmosphere and moisture absorbent material.
 - Please avoid rapid transitions in ambient temperature, especially, in high humidity environments where condensation can occur.
3. Soldering
 - Careful attention should be paid during soldering. When soldering, leave more then 3mm from solder joint to epoxy bulb, and soldering beyond the base of the tie bar is recommended.

■ Recommended soldering conditions:

Hand Soldering		DIP Soldering	
Temp. at tip of iron	300°C Max. (30W Max.)	Preheat temp.	100°C Max. (60 sec Max.)
Soldering time	3 sec Max.	Bath temp. & time	260 Max., 5 sec Max
Distance	3mm Min.(From solder joint to epoxy bulb)	Distance	3mm Min. (From solder joint to epoxy bulb)

■ Recommended soldering profile



■ Avoiding applying any stress to the lead frame while the Phototransistor are at high temperature particularly when soldering.

■ Dip and hand soldering should not be done more than one time

■ After soldering the Phototransistor, the epoxy bulb should be protected from mechanical shock or vibration until the Phototransistor return to room temperature.

■ A rapid-rate process is not recommended for cooling the Phototransistor down from the peak temperature.

Although the recommended soldering conditions are specified in the above table, dip or hand soldering at the lowest possible temperature is desirable for the Phototransistor.

■ Wave soldering parameter must be set and maintain according to recommended temperature and dwell time in the solder wave.

4. Cleaning

■ When necessary, cleaning should occur only with isopropyl alcohol at room temperature for a duration of no more than one minute. Dry at room temperature before use.

■ Do not clean the Phototransistor by the ultrasonic. When it is absolutely necessary, the influence of ultrasonic cleaning on the Phototransistor depends on factors such as ultrasonic power and the assemblPhototransistor condition. Ultrasonic cleaning shall be pre-qualified to ensure this will not cause damage to the PHOTOTRANSISTOR

5. Heat Management

■ Heat management of Phototransistor must be taken into consideration during the design stage of PHOTOTRANSISTOR application. The current should be de-rated appropriately by referring to the de-rating curve found in each product

specification.

- The temperature surrounding the PHOTOTRANSISTOR in the application should be controlled. Please refer to the data sheet de-rating curve.

6. ESD (Electrostatic Discharge)

- Electrostatic discharge (ESD) or surge current (EOS) can damage Phototransistor.
- An ESD wrist strap, ESD shoe strap or antistatic gloves must be worn whenever handling Phototransistor.
- All devices, equipment and machinery must be properly grounded.
- Use ion blower to neutralize the static charge which might have built up on surface of the Phototransistor plastic lens as a result of friction between Phototransistor during storage and handling.

DISCLAIMER

1. EVERLIGHT reserves the right(s) on the adjustment of product material mix for the specification.
2. The product meets EVERLIGHT published specification for a period of twelve (12) months from date of shipment.
3. The graphs shown in this datasheet are representing typical data only and do not show guaranteed values.
4. When using this product, please observe the absolute maximum ratings and the instructions for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from the use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
5. These specification sheets include materials protected under copyright of EVERLIGHT. Reproduction in any form is prohibited without obtaining EVERLIGHT's prior consent.
6. This product is not intended to be used for military, aircraft, automotive, medical, life sustaining or life saving applications or any other application which can result in human injury or death. Please contact authorized Everlight sales agent for special application request.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Phototransistors](#) category:

Click to view products by [Everlight](#) manufacturer:

Other Similar products are found below :

[LTR-5576D](#) [QSD123A4R0](#) [ASDL-6620-C22](#) [OED-ST-8LR2](#) [OED-STR44B90-TR](#) [SD5410-109](#) [PT91-21C/TR7](#) [L-51ROPT1D1](#) [PT928-6C\(X3-X5\)\(XBY\)](#) [PT908-7C\(BIN3\)](#) [PT19-21B/L41/TR8\(BY\)](#) [PT928-6C/F1\(6-1\)](#) [XYC-PT3020F65-L4](#) [DY-PT-8S302320B-6.5T](#) [DY-PTS302320B/6.5T](#) [XL-TD3216PDC](#) [MPT60363T\(SHW\)](#) [XYC-PT26B-L1](#) [XYC-PT2835F30-A4](#) [XYC-PT204B-L1](#) [XYC-PT17B-L1](#) [ZSPT-3216B-19D-T15](#) [ZSPT-3216C-19C-T15](#) [ZSPTP68C](#) [ZSPT0348B](#) [ZPT-Z3224B-T26-T15\(YPX\)](#) [ZSPT034B-N](#) [ZSPT034C-N](#) [PT67-21B/L606/TR8\(DVP-2\)](#) [PT8294-6B](#) [L-3DP3C](#) [XYC-PT3A940FC-A1](#) [XYC-PT19B-L1](#) [XYC-PT3216D25-A1](#) [XYC-PT3A940FC-A4](#) [XYC-PT3B850DC-A2](#) [XYC-PT3A850DC-A1](#) [XYC-PT5A850DC-A1](#) [XYC-PT3212D25-A1](#) [XYC-PT3A850DC-A2](#) [XYC-PT3A850DC-L1](#) [L32ROPT1D1](#) [ZSPT054B](#) [ZSPT868B-F14/H](#) [ZPT-3216B-19D-R15](#) [ZSPTP08C](#) [ZPT-1608B-06-Z4](#) [ZSPT054C](#) [ZSPTP28C](#) [BP 103-3/4](#)